

Fengqing Zhang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1631626/publications.pdf>

Version: 2024-02-01

22
papers

208
citations

1163117

8
h-index

1058476

14
g-index

22
all docs

22
docs citations

22
times ranked

157
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhanced leakage and ferroelectric properties of Zn-doped BiFeO ₃ thin films grown by sol-gel method. Journal of Alloys and Compounds, 2018, 734, 243-249.	5.5	52
2	Phase transition and multiferroic properties of Zr-doped BiFeO ₃ thin films. Journal of Materials Chemistry C, 2020, 8, 17307-17317.	5.5	24
3	Effects of transition metal (Cu, Zn, Mn) doped on leakage current and ferroelectric properties of BiFeO ₃ thin films. Journal of Materials Science: Materials in Electronics, 2017, 28, 14944-14948.	2.2	17
4	Effects of excess Bi on structure and electrical properties of BiFeO ₃ thin films deposited on indium tin oxide substrate using sol-gel method. Journal of Materials Science: Materials in Electronics, 2015, 26, 10095-10101.	2.2	14
5	Improved leakage and ferroelectric properties of Sr doped BiFe _{0.95} Mn _{0.05} O ₃ thin films. Journal of Materials Science: Materials in Electronics, 2016, 27, 6854-6858.	2.2	14
6	Modified ferroelectric and photovoltaic properties of BiFe _{0.91} Zr _{0.09} O ₃ thin films <i>via</i> altered annealing atmospheres. Journal of Materials Chemistry C, 2021, 9, 14659-14668.	5.5	12
7	The effect of the annealing atmosphere on the properties of Sr ₂ Bi ₄ Ti ₅ O ₁₈ ferroelectric thin films. Ceramics International, 2019, 45, 18320-18326.	4.8	10
8	Study of the properties of SBT ceramics doped with different concentrations of Ca. Ceramics International, 2018, 44, 21914-21920.	4.8	8
9	Effect of the thickness of Sr ₂ Bi ₄ Ti ₅ O ₁₈ transition layer on the properties of BiFeO ₃ /Sr ₂ Bi ₄ Ti ₅ O ₁₈ bilayer composite thin films. Ceramics International, 2020, 46, 10536-10544.	4.8	8
10	Effects of precursor concentration on electric properties of BiFe _{0.98} Mn _{0.02} O ₃ thin films prepared by sol-gel method. Journal of Sol-Gel Science and Technology, 2018, 85, 158-165.	2.4	6
11	Phase Structure and Electrical Properties of Sm-Doped BiFe _{0.98} Mn _{0.02} O ₃ Thin Films. Nanomaterials, 2022, 12, 108.	4.1	6
12	The effect of sintering atmospheres on the properties of CSBT-0.15 ferroelectric ceramics. Ceramics International, 2018, 44, 13502-13506.	4.8	5
13	Perfection of leakage and ferroelectric properties of Ni-doped BiFeO ₃ thin films. Micro and Nano Letters, 2018, 13, 502-505.	1.3	5
14	Structure and electrical properties of Zn-doped BiFeO ₃ films. International Journal of Applied Ceramic Technology, 2020, 17, 1392-1399.	2.1	5
15	Study on properties of BiFe _{0.98} Mn _{0.02} O ₃ /Sr ₂ Bi ₄ Ti ₅ O ₁₈ double-layer composite films. Journal of Alloys and Compounds, 2020, 836, 155433.	5.5	5
16	Effects of the annealing atmosphere on the microstructure and properties of BiFe _{0.99} Zn _{0.01} O ₃ films. Ceramics International, 2020, 46, 4314-4321.	4.8	4
17	Properties of neodymium-doped Ca _{0.15} Sr _{1.85} Bi ₄ Ti ₅ O ₁₈ ferroelectric ceramics. Journal of Materials Science: Materials in Electronics, 2011, 22, 1778-1782.	2.2	3
18	Preparation and Growth of Predominantly (100)-Oriented Ca _{0.4} Sr _{0.6} Bi ₄ Ti ₅ O ₁₈ Thin Film by Rapid Thermal Annealing. Journal of the American Ceramic Society, 2012, 95, 1889-1893.		

#	ARTICLE	IF	CITATIONS
19	Structure and electrical conductivity of 0.5CSBT-0.5BFO ceramics sintered in air and N ₂ . Ceramics International, 2022, 48, 14442-14450.	4.8	3
20	PREPARATION AND FERROELECTRIC PROPERTY OF (100)-ORIENTED $\text{Ca}_{0.4}\text{Sr}_{0.6}\text{Bi}_4\text{Ti}_4\text{O}_{15}$ THIN FILM ON $\text{Pt}/\text{Ti}/\text{SiO}_2/\text{Si}$ SUBSTRATE. Surface Review and Letters, 2010, 17, 445-449.	1.1	2
21	Effect of annealing temperature on the properties of 0.5Bi ₄ Ti ₃ O ₁₂ -0.5BiFe _{0.98} Mn _{0.02} O ₃ thin films. Ceramics International, 2022, , .	4.8	2
22	Effect of Ca doping on the properties of Sr ₂ Bi ₄ Ti ₅ O ₁₈ ferroelectric thin films. Journal of Materials Science: Materials in Electronics, 2019, 30, 13434-13444.	2.2	0